

N-channel TrenchMOS standard level FET Rev. 02 — 27 January 2011

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Suitable for standard level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	62	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	115	W
Static cha	aracteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ T _j = 25 °C; see <u>Figure 11;</u> see Figure 12		-	13	15	mΩ



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Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e Ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 62 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ T_{\text{j(init)}} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$	-	-	211	mJ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 44 V; T _j = 25 °C; see <u>Figure 13</u>	-	19	-	nC

SOT428 (DPAK)

[1] Current is limited by power dissipation chip rating.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7215-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

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4. Limiting values

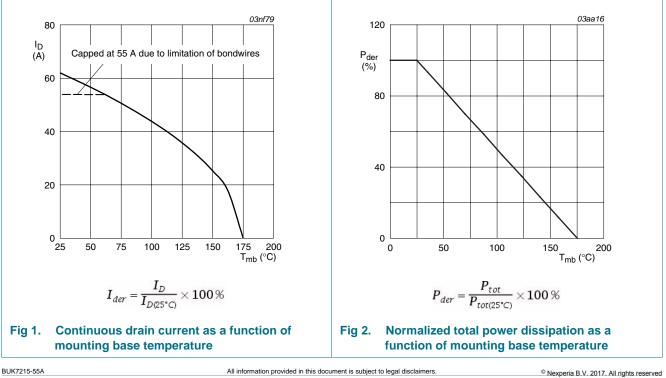
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \ k\Omega$		-	55	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	44	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } Figure 3;$	[1]	-	62	А
		see <u>Figure 1</u>	[2]	-	55	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>		-	248	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	115	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
Is	source current	T _{mb} = 25 °C	[1]	-	62	А
			[2]	-	55	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	248	А
Avalanche I	Ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 62 A; V _{sup} ≤ 55 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped		-	211	mJ
		· · ·				

[1] Current is limited by power dissipation chip rating.

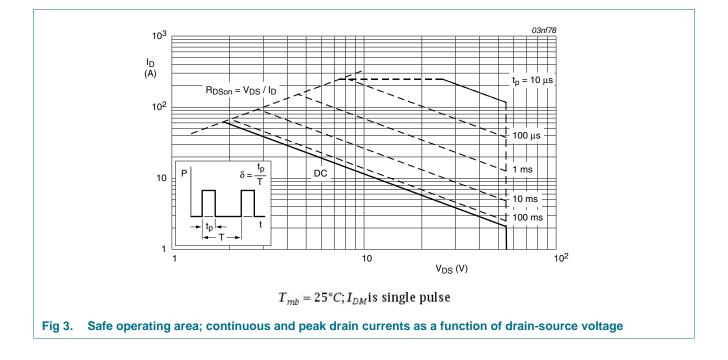
[2] Continuous current is limited by bond wires.



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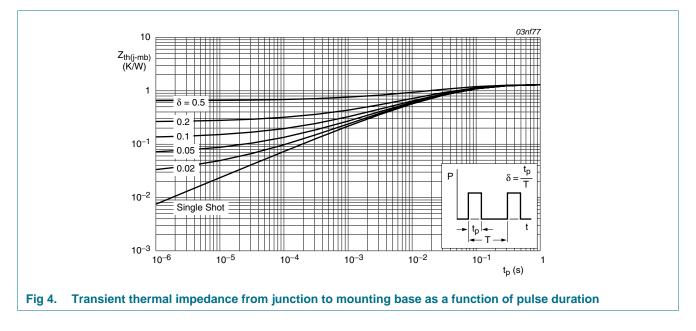
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	1.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; FR4 printed circuit board	-	71.4	-	K/W



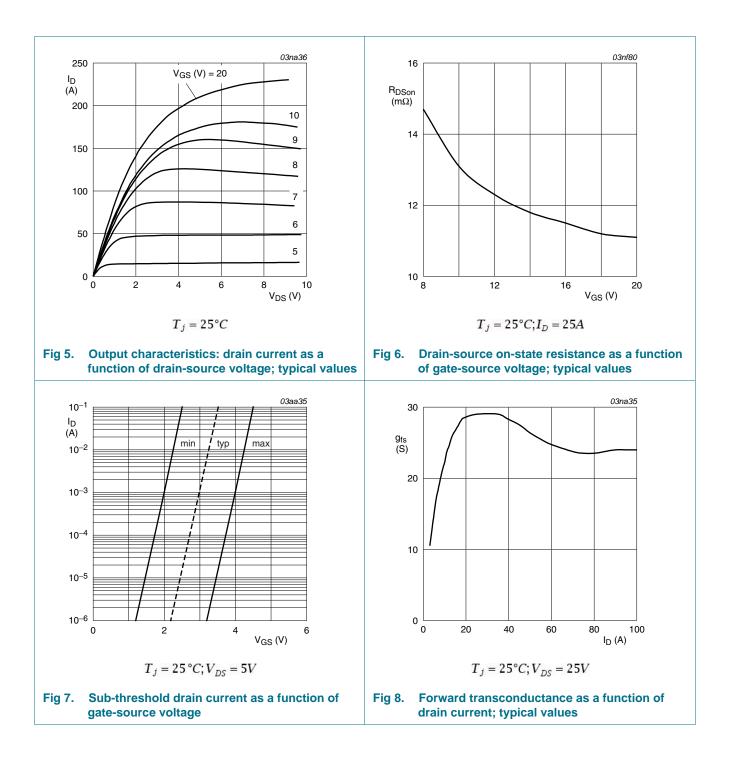
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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	30	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11; see Figure 12	-	13	15	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	50	-	nC
Q_{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } Figure 13$	-	9	-	nC
Q_{GD}	gate-drain charge		-	19	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1580	2107	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	370	446	pF
C _{rss}	reverse transfer capacitance		-	220	300	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	26	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	99	-	ns
t _{d(off)}	turn-off delay time		-	73	-	ns
t _f	fall time		-	65	-	ns
L _D	internal drain inductance	measured from drain to centre of die ; $T_{j}=25\ ^{\circ}\text{C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = -100 A/µs;	-	48	-	ns
Qr	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	106	-	nC

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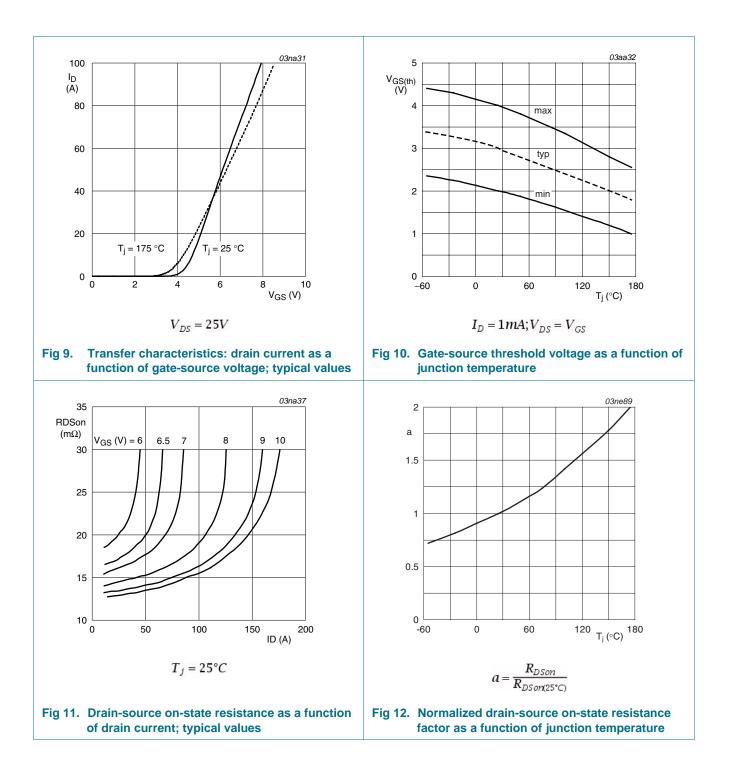


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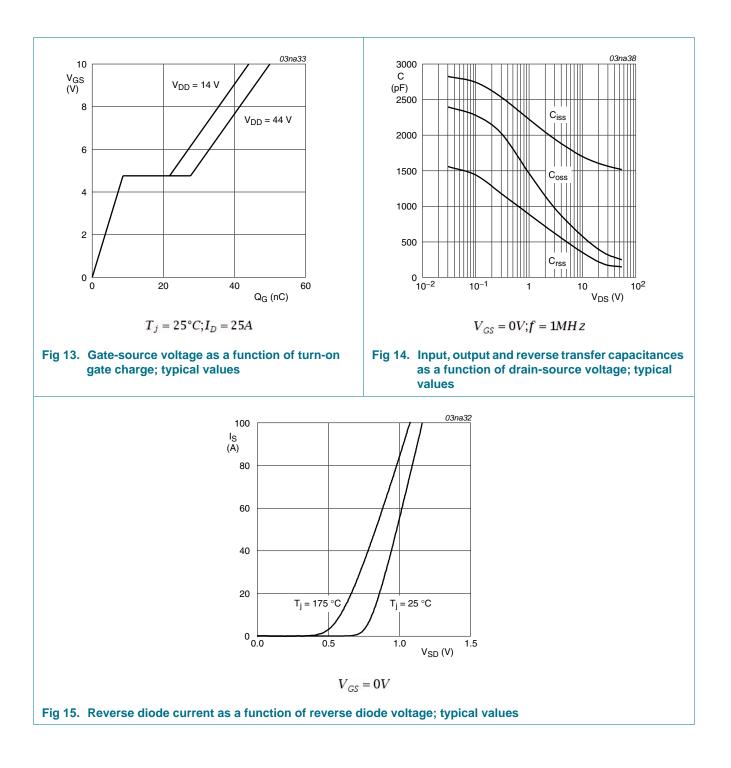


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7. Package outline

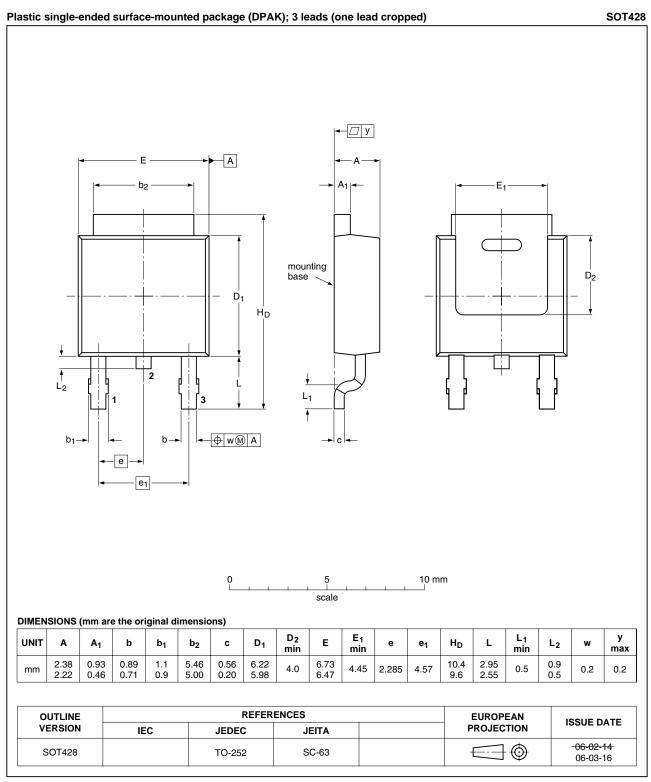


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7215-55A v.2	20110127	Product data sheet	-	BUK7215_55A v.1
Modifications:	 The format of of NXP Semic 	this data sheet has been re- onductors.	designed to comply with	the new identity guidelines
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.
BUK7215_55A v.1	20010816	Product data	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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